VN2406L

Preferred Device

Small Signal MOSFET 200 mAmps, 240 Volts

N-Channel TO-92

MA

| MAXIMUM RATINGS | | | | | |
|------------------------------------------------------------------------------------|-------------------------------------|--------------|-------------|--|--|
| Rating | Symbol | Value | Unit | | |
| Drain-Source Voltage | V _{DSS} | 240 | Vdc | | |
| Drain-Gate Voltage | V _{DGR} | 240 | Vdc | | |
| Gate – Source Voltage – Continuous – Non−repetitive (t _p ≤ 50 μs) | V _{GS} V _{GSM} | ± 20 ± 40 | Vdc Vpk | | |
| Continuous Drain Current | Ι _D | 200 | mAdc | | |
| Pulsed Drain Current | I _{DM} | 500 | mAdc | | |
| Power Dissipation @ T _C = 25°C Derate above 25°C | PD | 350 2.8 | mW mW/°C | | |
| Operating and Storage Temperature | T _J , T _{stg} | - | °C | | |
| | | | | | |

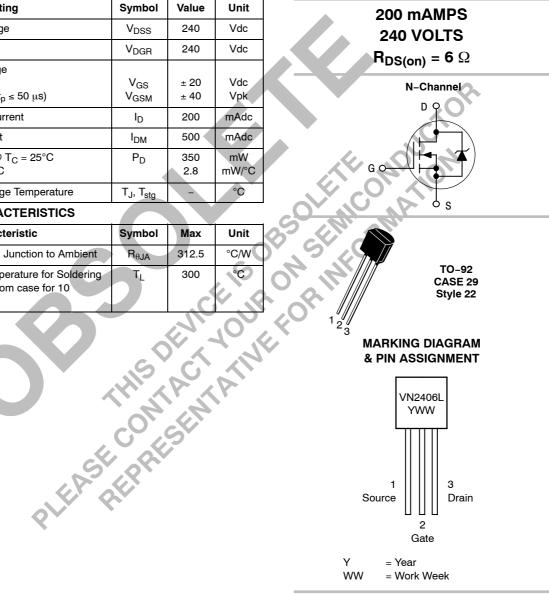
THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---------------------------------------------------------------------------------------|------------------|-------|------|
| Thermal Resistance, Junction to Ambient | R _{θJA} | 312.5 | °C/W |
| Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds | TL | 300 | ç |



ON Semiconductor™

http://onsemi.com



ORDERING INFORMATION

| Device | Package | Shipping | | |
|------------|---------|----------------|--|--|
| VN2406L | TO-92 | 1000 Units/Box | | |
| VN2406LZL1 | TO-92 | 2000 Ammo Pack | | |

Preferred devices are recommended choices for future use and best overall value.

VN2406L

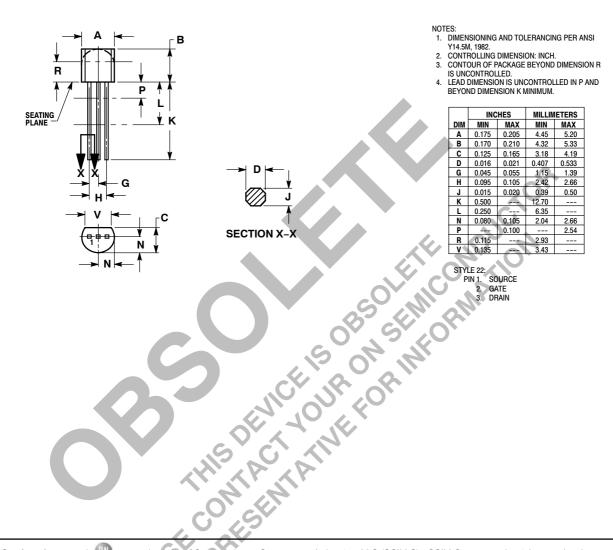
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| | Characteristic | Symbol | Min | Max | Unit |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------|----------------------|-----|-----------|------|
| STATIC CHARACTERISTICS | | | | | |
| Drain – Source Breakdown Voltag $(V_{GS} = 0, I_D = 100 \ \mu A)$ | 9 | V _{(BR)DSS} | 240 | - | Vdc |
| Zero Gate Voltage Drain Current $(V_{DS} = 120 \text{ Vdc}, V_{GS} = 0)$ $(V_{DS} = 120 \text{ Vdc}, V_{GS} = 0, T_A =$ | 125°C) | I _{DSS} | | 10 500 | μAdc |
| Gate- Body Leakage $(V_{DS} = 0, V_{GS} = \pm 15 \text{ V})$ | | I _{GSS} | - | ±100 | nAdc |
| Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = 1.0 \text{ mA})$ | | V _{GS(th)} | 0.8 | 2.0 | Vdc |
| On–State Drain Current (Note 1) (V _{GS} = 10 V, V _{DS} ≥ 2.0 V _{DS(on)} | | I _{D(on)} | 1.0 | - | Adc |
| $\label{eq:VGS} \begin{array}{l} \mbox{Drain-Source On Resistance (No (V_{GS} = 2.5 \ \mbox{V}, \ \mbox{I}_D = 0.1 \ \mbox{A}) \\ \mbox{(V}_{GS} = 10 \ \mbox{V}, \ \mbox{I}_D = 0.5 \ \mbox{A}) \end{array}$ | te 1) | r _{DS(on)} | - | 10 6.0 | Ω |
| Forward Transconductance (Note (V_{DS} = 10 V, I_D = 0.5 A) | 1) | 9 _{fs} | 300 | - | mS |
| DYNAMIC CHARACTERISTIC | s | | | 2 | |
| Input Capacitance | | C _{iss} | N-1 | 125 | pF |
| Output Capacitance | (V _{DS} = 25 Vdc, V _{GS} = 0, f = 1.0 MHz) | C _{oss} | | 50 | pF |
| Reverse Transfer Capacitance | | Crss | | 20 | pF |
| SWITCHING CHARACTERIS | rics | 64.0 | C | | |
| Turn-On Time | 6 | t _(on) | _ | 8.0 | ns |
| | (V _{DD} = 60 Vdc, I _D = 0.4 A, R _L = 150 Ω, R _G = 25 Ω) | t(r) | - | 8.0 | ns |
| Turn-Off Time | | t _(off) | - | 23 | ns |
| | | t _(f) | _ | 34 | ns |
| | s, Duty Cycle ≤ 2.0%. | | | | |

VN2406L

PACKAGE DIMENSIONS

TO-92 CASE 29-11 ISSUE AL



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